

**SEMICONDUCTOR
TECHNICAL DATA**

KTB2510

EPITAXIAL PLANAR PNP TRANSISTOR

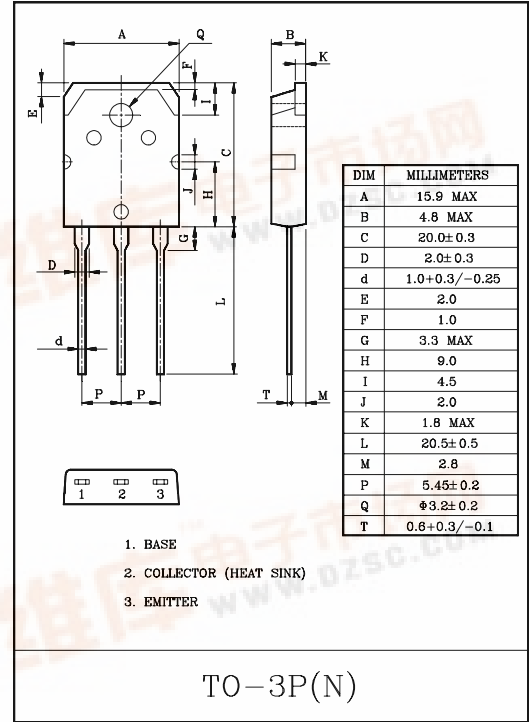
HIGH POWER AMPLIFIER
DARLINGTON APPLICATION.

FEATURES

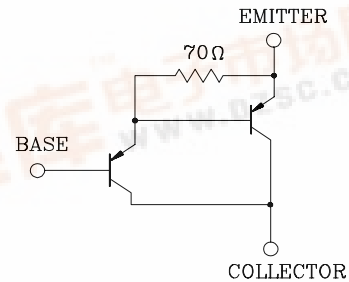
- Complementary to KTD1510
- Recommended for 60W Audio Amplifier Output Stage.

MAXIMUM RATINGS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---------------------------------------|------------------|---------|------|
| Collector-Base Voltage | V _{CBO} | -160 | V |
| Collector-Emitter Voltage | V _{CEO} | -150 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Collector Current | I _C | -10 | A |
| Base Current | I _B | -1 | A |
| Collector Power Dissipation (Tc=25°C) | P _C | 100 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | -55~150 | °C |



EQUIVALENT CIRCUIT

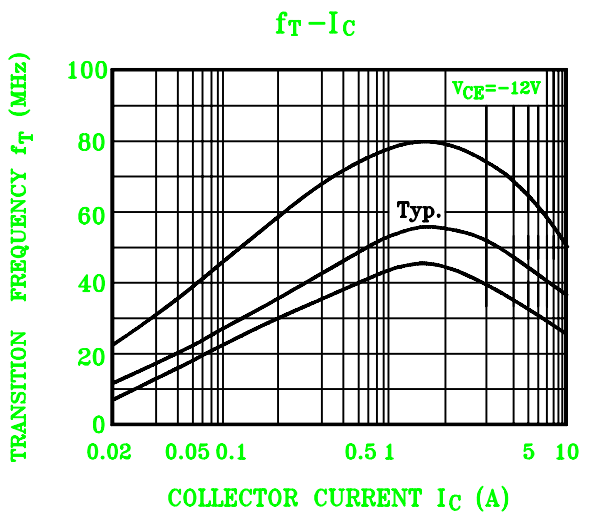
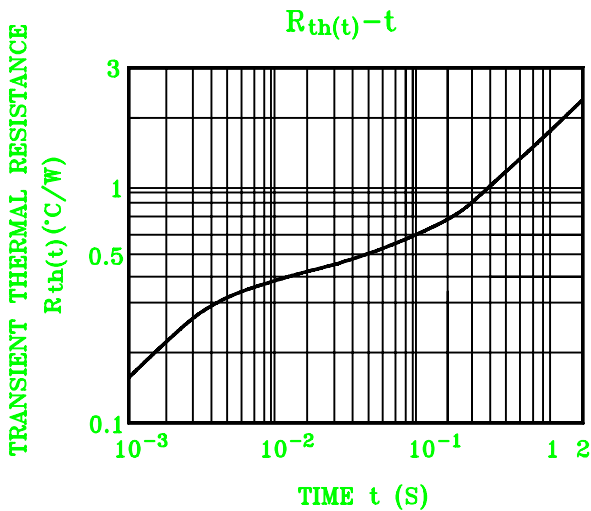
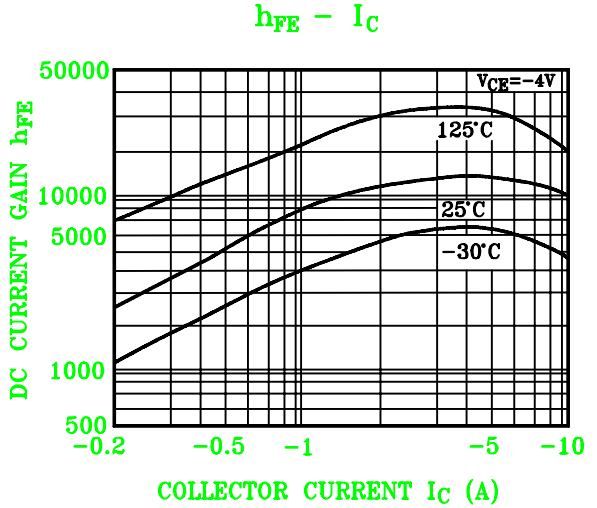
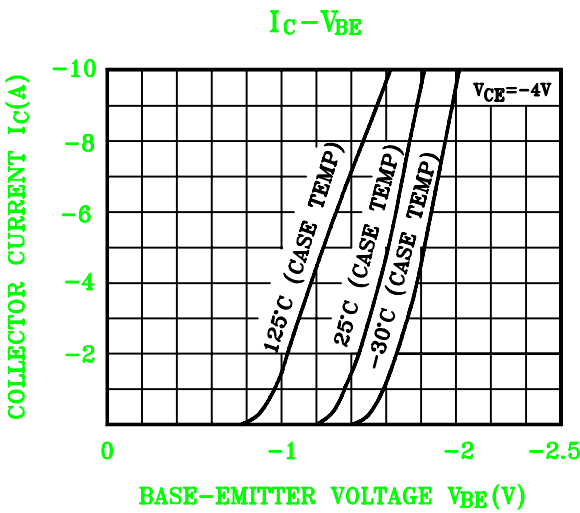
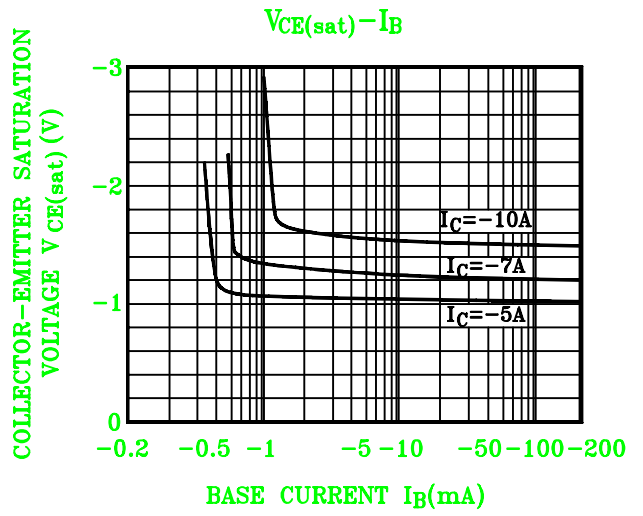
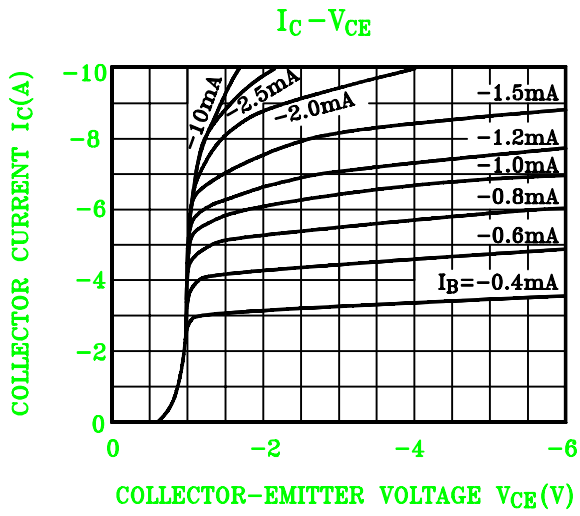


ELECTRICAL CHARACTERISTICS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|----------------------|---|------|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} =-160V | - | - | -100 | μA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} =-5V | - | - | -100 | μA |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | I _C =-30mA | -150 | - | - | V |
| DC Current Gain | h _{FE} | V _{CE} =-4V, I _C =-7A | 5000 | - | - | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =-7A, I _B =-7mA | - | - | -2.5 | V |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | I _C =-7A, I _B =-7mA | - | - | -3.0 | V |
| Transition Frequency | f _T | V _{CE} =-12V, I _C =2A | - | 50 | - | MHz |
| Collector Output Capacitance | C _{ob} | V _{CB} =-10V, f=1MHz | - | 230 | - | pF |

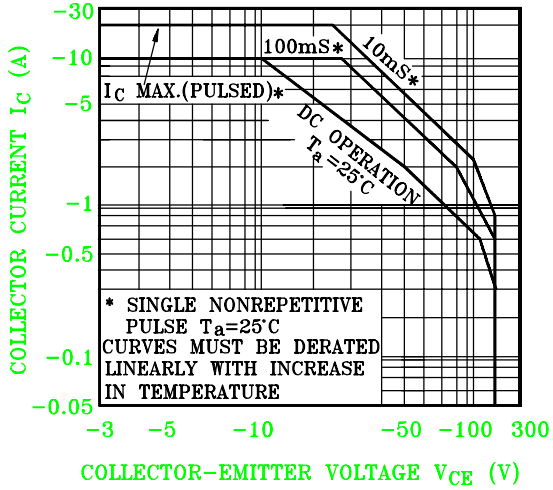


KTB2510



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SAFE OPERATING AREA



$P_C - T_a$

